# **PNP Silicon Epitaxial Transistor**

This PNP Silicon Epitaxial Transistor is designed for use in low voltage, high current applications. The device is housed in the SOT-223 package, which is designed for medium power surface mount applications.

## **Features**

- High Current:  $I_C = -1.0 \text{ A}$
- The SOT-223 Package Can Be Soldered Using Wave or Reflow.
- SOT-223 package ensures level mounting, resulting in improved thermal conduction, and allows visual inspection of soldered joints. The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die.
- NPN Complement is BCP68
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## **MAXIMUM RATINGS** (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	-20	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-25	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current	I <sub>C</sub>	-1.0	Adc
Total Power Dissipation @ T <sub>A</sub> = 25°C (Note 1) Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to 150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance – Junction–to–Ambient (Surface Mounted)	$R_{\theta JA}$	83.3	°C/W
Lead Temperature for Soldering, 0.0625 in from case	TL	260	°C
Time in Solder Bath		10	s

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 sq. in.

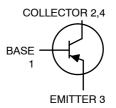
1



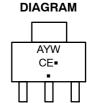
## ON Semiconductor®

http://onsemi.com

**MEDIUM POWER** PNP SILICON **HIGH CURRENT TRANSISTOR** SURFACE MOUNT







**MARKING** 

CE = Specific Device Code

= Assembly Location

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
BCP69T1G	SOT-223 (Pb-Free)	1000 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = –100 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CES</sub>	-25	-	_	Vdc		
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-20	-	-	Vdc		
Emitter-Base Breakdown Voltage ( $I_E = -10 \mu Adc$ , $I_C = 0$ )	V <sub>(BR)EBO</sub>	-5.0	-	-	Vdc		
Collector-Base Cutoff Current (V <sub>CB</sub> = -25 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	-10	μAdc		
Emitter-Base Cutoff Current (V <sub>EB</sub> = -5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-	-10	μAdc		
ON CHARACTERISTICS							
DC Current Gain ( $I_C = -5.0$ mAdc, $V_{CE} = -10$ Vdc) ( $I_C = -500$ mAdc, $V_{CE} = -1.0$ Vdc) ( $I_C = -1.0$ Adc, $V_{CE} = -1.0$ Vdc)	h <sub>FE</sub>	50 85 60	- - -	- 375 -	-		
Collector-Emitter Saturation Voltage (I <sub>C</sub> = -1.0 Adc, I <sub>B</sub> = -100 mAdc)	V <sub>CE(sat)</sub>	-	-	-0.5	Vdc		
Base–Emitter On Voltage (I <sub>C</sub> = -1.0 Adc, V <sub>CE</sub> = -1.0 Vdc)	V <sub>BE(on)</sub>	-	-	-1.0	Vdc		
DYNAMIC CHARACTERISTICS							
Current–Gain – Bandwidth Product $(I_C = -10 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	f <sub>T</sub>	-	60	_	MHz		

## TYPICAL ELECTRICAL CHARACTERISTICS

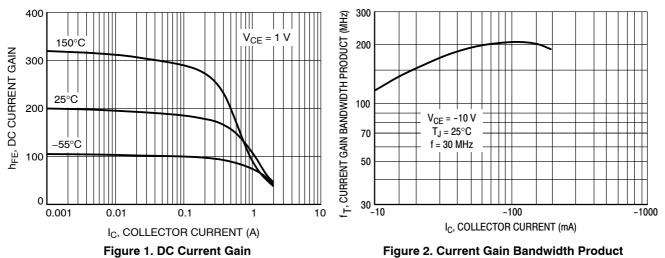


Figure 2. Current Gain Bandwidth Product

## TYPICAL ELECTRICAL CHARACTERISTICS

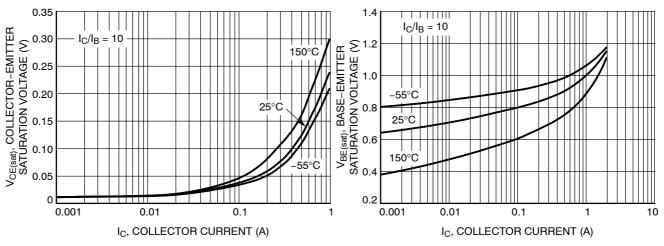


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

Figure 4. Base Emitter Saturation Voltage vs.

Collector Current

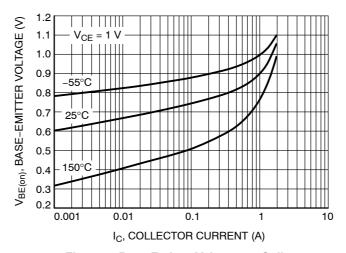


Figure 5. Base Emitter Voltage vs. Collector
Current

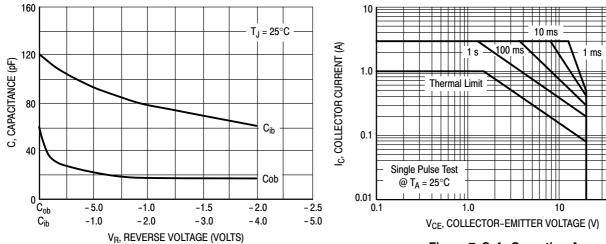


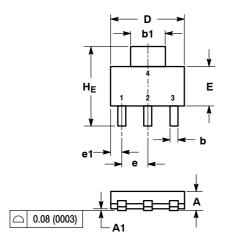
Figure 6. Capacitances

Figure 7. Safe Operating Area

100

### PACKAGE DIMENSIONS

## **SOT-223 (TO-261)** CASE 318E-04 ISSUE N





NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M,

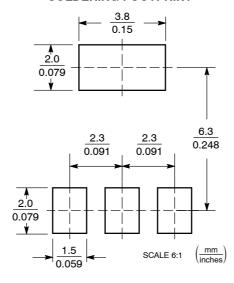
2. CONTROLLING DIMENSION: INCH.							
	MILLIMETERS				INCHES		
DIM	MIN	NOM	MAX	MIN	MON	MAX	
Α	1.50	1.63	1.75	0.060	0.064	0.068	
A1	0.02	0.06	0.10	0.001	0.002	0.004	
b	0.60	0.75	0.89	0.024	0.030	0.035	
b1	2.90	3.06	3.20	0.115	0.121	0.126	
C	0.24	0.29	0.35	0.009	0.012	0.014	
D	6.30	6.50	6.70	0.249	0.256	0.263	
E	3.30	3.50	3.70	0.130	0.138	0.145	
е	2.20	2.30	2.40	0.087	0.091	0.094	
e1	0.85	0.94	1.05	0.033	0.037	0.041	
L	0.20			0.008			
L1	1.50	1.75	2.00	0.060	0.069	0.078	
HE	6.70	7.00	7.30	0.264	0.276	0.287	
θ	0°	-	10°	0°	-	10°	

STYLE 1:

PIN 1. BASE 2. COLLECTOR 3. EMITTER

4. COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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